CLAIMS

[1] A composition for formation of etching stopper layer, comprising a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing polymer in the composition, of silicon is contained in a disilylbenzene structure.

[2] The composition for formation of etching stopper layer according to claim 1, wherein said silicon-containing polymer has been produced by polymerizing a compound having a disilylbenzene structure and an aromatic group-containing compound.

[3] A silicon-containing material for formation of etching stopper layer, comprising a disilylbenzene structure formed by curing a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing material, of silicon is contained in a disilylbenzene structure.

[4] A semiconductor device comprising, as an etching stopper layer, a silicon-containing material for formation of etching stopper layer according to claim 3.

[5] A process for producing a semiconductor device, comprising the steps of: forming an insulating layer and an etching stopper layer on a substrate; removing part of the insulating layer by dry etching; and filling an electrically conductive material into a groove or hole thus formed, wherein said etching stopper layer is formed by curing a composition comprising a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing polymer, of silicon is contained in a disilylbenzene structure.